

SEMICONDUCTOR®

MMBT3646

Switching Transistor



1. Base 2. Emitter 3. Collector

Absolute Maximum Ratings T_{C} =25°C unless otherwise noted

Symbol	Parameter	Value	Units V	
V _{CEO}	Collector-Emitter Voltage	15		
V _{CES}	Collector-Emitter Voltage	40	V	
V _{CBO}	Collector-Base Voltage	40	V	
V _{EBO}	Emitter-Base Voltage	5		
I _C	Collector Current (DC) - Continuous	300	mA	
P _D	Total Device Dissipation @ T _A =25°C - Derate above 25°C	625 5	mW mW/°C	
T _J , T _{STG}	Operating and Storage Junction Temperature Range	150	°C	

Electrical Characteristics $T_C=25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Min.	Тур.	Max.	Units
Off Characte	ristics				
V _{(BR)CES}	Collector-Emitter Breakdown Voltage ($I_c = 100\mu$ Adc, $V_{BE} = 0$)	40			V
V _{CEO(SUS)}	Collector-Emitter Sustaining Voltage (1) ($I_c = 10$ mAdc, $I_B = 0$)	15			V
V _{(BR)CBO}	Collector-Base Breakdown Voltage ($I_c = 100 \mu Adc$, $I_E = 0$)	40			V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage ($I_E = 100 \mu Adc$, $I_C = 0$)	5			V
ICES	Collector Cut-off Current (V _{CE} = 20Vdc, V _{BE} = 0)			0.5	μA
	$(V_{CE} = 20Vdc, V_{BE} = 0, T_A = 65^{\circ}C)$			3	
On Characte	ristics (1)				
h _{FE}	DC Current Gain (I _C = 30mAdc, V _{CE} = 0.4Vdc)	30		120	
	$(I_C = 100 \text{mAdc}, V_{CE} = 0.5 \text{Vdc})$	25			
	$(I_{C} = 300 \text{mAdc}, V_{CE} = 1 \text{Vdc})$	15			
V _{CE(sat)}	Collector-Emitter Saturation Voltage (I _C = 30mAdc, I _B = 3mAdc)			0.2	V
· · ·	$(I_{C} = 100 \text{mAdc}, I_{B} = 10 \text{mAdc})$			0.28	
	$(I_{C} = 300 \text{mAdc}, I_{B} = 30 \text{mAdc})$			0.5	
	(I _C = 30mA, I _B = 3mA, T _A =65°C)			0.3	
V _{BE(sat)}	Base-Emitter Saturation Voltage (I _C = 30mAdc, I _B = 3mAdc)	0.73		0.95	V
()	$(I_{C} = 100 \text{mAdc}, I_{B} = 10 \text{mAdc})$			1.2	
	$(I_{C} = 300 \text{mAdc}, I_{B} = 30 \text{mAdc})$			1.7	

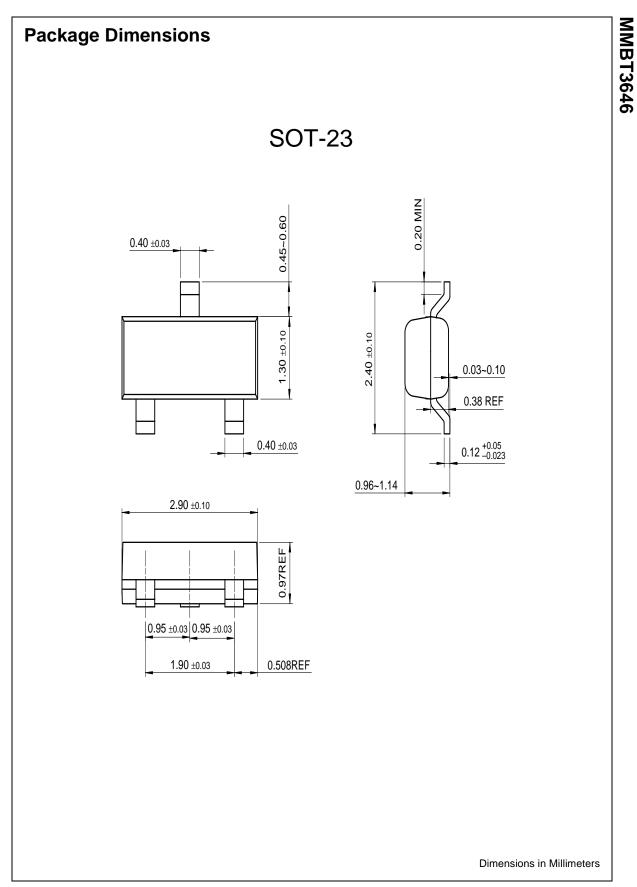
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Symbol		Parameter			Max.	Units
Small-Signal	Characteristics					
C _{obo}	Output Capacitance (V _{CE} = 5Vdc, I _E = 0, f = 1MHz)				5	pF
C _{ibo}	Input Capacitance (V _{EB} = 0.5Vdc, I _C = 0, f = 1MHz)				8	pF
Switching Ch	aracteristics					
t _{on}	Turn-On Time	$V_{CC} = 10$ Vdc, $I_C = 300$ mAdc,			18	ns
t _d	Delay Time	$I_{B1} = 30 \text{mAdc}, V_{CE(off)} = 3 \text{V}$			10	ns
t _r	Rise Time				15	ns
t _{off}	Turn-Off Time	$V_{CC} = 10Vdc, I_C = 300mAdc,$			28	ns
t _f	Fall Time	$I_{B1} = I_{B2} = 30 \text{mAdc}$			15	ns
t _s	Storge Time				20	ns

Thermal Characteristics

Symbol	Parameter	Min.	Тур.	Max.	Units
$R_{ extsf{ heta}JA}$	Thermal Resistance, Junction to Ambient			200	°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case			83.3	°C



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